74HC40103

8-bit synchronous binary down counter

Rev. 4 — 27 January 2016

1. General description

The 74HC40103 is an 8-bit synchronous down counter. It has control inputs for enabling or disabling the clock (CP), for clearing the counter to its maximum count and for presetting the counter either synchronously or asynchronously. In normal operation, the counter is decremented by one count on each positive-going transition of the clock (CP). Counting is inhibited when the terminal enable input (TE) is HIGH. The terminal count output (TC) goes LOW when the count reaches zero if TE is LOW, and remains LOW for one full clock period. When the synchronous preset enable input (PE) is LOW, data at the jam input (P0 to P7) is clocked into the counter on the next positive-going clock transition regardless of the state of TE. When the asynchronous preset enable input (PL) is LOW, data at the jam input (P0 to P7) is asynchronously forced into the counter regardless of the state of PE, TE, or CP. The jam inputs (P0 to P7) represent a single 8-bit binary word. When the master reset input (MR) is LOW, the counter is asynchronously cleared to its maximum count (decimal 255) regardless of the state of any other input. If all control inputs except TE are HIGH at the time of zero count, the counters will jump to the maximum count, giving a counting sequence of 256 clock pulses long. Device may be cascaded using the TE input and the TC output, in either a synchronous or ripple mode. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

2. Features and benefits

- Cascadable
- Synchronous or asynchronous preset
- Low-power dissipation
- Complies with JEDEC standard no. 7A
- Input levels:
 - For 74HC40103: CMOS level
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +80 °C and from -40 °C to +125 °C

3. Applications

- Divide-by-n counters
- Programmable timers
- Interrupt timers



Cycle/program counters.

4. Ordering information

Table 1.Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74HC40103D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1					
74HC40103DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1					
74HC40103PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1					

5. Functional diagram



74HC40103



0 255 254 254 253 8

7 6

5 4 255 254 253 252

001aab925

Fig 4. Timing diagram

P5 P6 P7 TC

count

255 254 3

2 1

74HC40103 Product data sheet

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8-bit synchronous binary down counter 74HC40103

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Fig 5. Logic diagram

TE -

to other 7 flip-flops

6. Pinning information

6.1 Pinning



6.2 Pin description

Symbol	Pin	Description
CP	1	clock input (LOW-to-HIGH, edge-triggered)
MR	2	asynchronous master reset input (active LOW)
TE	3	terminal enable input (active LOW)
P0	4	jam input 0
P1	5	jam input 1
P2	6	jam input 2
P3	7	jam input 3
GND	8	ground (0 V)
PL	9	asynchronous preset enable input (active LOW)
P4	10	jam input 4
P5	11	jam input 5
P5	12	jam input 6
P7	13	jam input 7
TC	14	terminal count output (active LOW)
PE	15	synchronous preset enable input (active LOW)
V _{CC}	16	positive supply voltage

7. Functional description

7.1 Function table

Table 3. Function table^[1]

Contro	Control inputs			Preset mode	Action ^[2]
MR	PL	PE	TE		
L	Х	Х	Х	asynchronous	clear to maximum count
Н	L	Х	Х	asynchronous	preset asynchronously
	Н	L	Х	synchronous	preset on next LOW-to HIGH clock transition
		Н	L	synchronous	count down
			Н	synchronous	inhibit counter

[1] H = HIGH voltage level;L = LOW voltage level;

X = don't care.

[2] Clock connected to CP.
 Synchronous operation: changes occur on the LOW-to-HIGH CP transition.
 Jam inputs: MSD = P7, LSD = P0.

8. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+7	V
I _{IK}	input clamping current	V_{I} < -0.5 V or V_{I} > V_{CC} + 0.5 V	<u>[1]</u>	-	±20	mA
I _{OK}	output clamping current	V_{O} < -0.5 V or V_{O} > V_{CC} + 0.5 V	<u>[1]</u>	-	±20	mA
lo	output current	$V_{\rm O}$ = –0.5 V to $V_{\rm CC}$ + 0.5 V		-	±25	mA
I _{CC}	supply current			-	+50	mA
I _{GND}	ground current			-50	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	SO16 package	[2]	-	500	mW
		SSOP16 and TSSOP16 packages	<u>[3]</u>	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO16 packages: above 70 $^\circ\text{C},$ P_tot derates linearly with 8 mW/K.

[3] For SSOP16 and TSSOP16 packages: above 60 °C, Ptot derates linearly with 5.5 mW/K.

9. Recommended operating conditions

Table 5.	Recommended	operating	conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		2.0	5.0	6.0	V
VI	input voltage		0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	V
$\Delta t / \Delta V$	input transition rise and	V _{CC} = 2.0 V	-	-	625	ns
	fall rates	V _{CC} = 4.5 V	-	1.67	139	ns
		$V_{CC} = 6.0 V$	-	-	83	ns
T _{amb}	ambient temperature		-40	-	+125	°C

10. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 25	°C					
VIH	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	V
VIL	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O} = -20 \ \mu A; \ V_{CC} = 2.0 \ V$	1.9	2.0	-	V
		$I_{O} = -20 \ \mu A; \ V_{CC} = 4.5 \ V$	4.4	4.5	-	V
		$I_{O} = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	V
		$I_0 = -4 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_0 = 20 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	V
		$I_0 = 4 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.26	V
li .	input leakage current	$V_1 = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	±0.1	μA
I _{CC}	supply current	$V_{I} = V_{CC}$ or GND; $I_{O} = 0$ A; $V_{CC} = 6.0$ V	-	-	8.0	μA
CI	input capacitance		-	3.5	-	pF

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -40) °C to +85 °C		I	1	1	
V _{IH}	HIGH-level input voltage	$V_{CC} = 2.0 V$	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		$V_{CC} = 6.0 V$	-	-	1.8	V
V _{ОН}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_0 = -20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.9	-	-	V
		$I_0 = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	-	-	V
		$I_{O} = -20 \ \mu\text{A}; \ V_{CC} = 6.0 \ \text{V}$	5.9	-	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.84	-	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.34	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_0 = 20 \ \mu A; \ V_{CC} = 2.0 \ V$	-	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	-	0.1	V
		$I_0 = 4 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.33	V
		$I_0 = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	-	0.33	V
I	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	±1.0	μA
сс	supply current	$V_{I} = V_{CC}$ or GND; $I_{O} = 0$ A; $V_{CC} = 6.0$ V	-	-	80	μA
Γ _{amb} = -40) °C to +125 °C		I			
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		$V_{CC} = 6.0 V$	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O} = -20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.9	-	-	V
		$I_{O} = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	-	-	V
		$I_{O} = -20 \ \mu\text{A}; \ V_{CC} = 6.0 \ \text{V}$	5.9	-	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.7	-	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.2	-	-	V

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O} = 20 \ \mu A; \ V_{CC} = 2.0 \ V$	-	-	0.1	V
		$I_{O} = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	-	0.1	V
		$I_{O} = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	-	0.1	V
		$I_0 = 4 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.4	V
		$I_0 = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	-	0.4	V
l _l	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	±1.0	μA
I _{CC}	supply current	$V_{I} = V_{CC}$ or GND; $I_{O} = 0$ A; $V_{CC} = 6.0$ V	-	-	160	μΑ

11. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; $t_r = t_f = 6 ns$; $C_L = 50 pF$; see <u>Figure 13</u>.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 25	°C					
pd	propagation delay	CP to TC; see Figure 7 [1]				
		V _{CC} = 2.0 V	-	96	300	ns
		V _{CC} = 4.5 V	-	35	60	ns
		V _{CC} = 6.0 V	-	28	51	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$	-	30	-	ns
		TE to TC; see Figure 8				
		V _{CC} = 2.0 V	-	50	175	ns
		V _{CC} = 4.5 V	-	18	35	ns
		V _{CC} = 6.0 V	-	14	30	ns
		PL to TC; see Figure 9				
		V _{CC} = 2.0 V	-	102	315	ns
		V _{CC} = 4.5 V	-	37	63	ns
		V _{CC} = 6.0 V	-	30	53	ns
PHL	HIGH to LOW	MR to TC; see Figure 9				
	propagation delay	V _{CC} = 2.0 V	-	83	275	ns
		V _{CC} = 4.5 V	-	30	55	ns
		V _{CC} = 6.0 V	-	24	47	ns
t	transition time	see Figure 8 [2]				
		V _{CC} = 2.0 V	-	19	75	ns
		V _{CC} = 4.5 V	-	7	15	ns
		$V_{CC} = 6.0 V$	-	6	13	ns

Table 7. Dynamic characteristics ...continued

GND = 0 V; $t_r = t_f = 6 ns$; $C_L = 50 pF$; see <u>Figure 13</u>.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _W	pulse width	CP HIGH or LOW; see Figure 7				
		V _{CC} = 2.0 V	165	22	-	ns
		$V_{CC} = 4.5 V$	33	8	-	ns
		V _{CC} = 6.0 V	28	6	-	ns
		MR LOW; see Figure 9				
		V _{CC} = 2.0 V	125	39	-	ns
		V _{CC} = 4.5 V	25	14	-	ns
		V _{CC} = 6.0 V	21	11	-	ns
		PL LOW; see Figure 9				
		V _{CC} = 2.0 V	125	33	-	ns
		V _{CC} = 4.5 V	25	12	-	ns
		V _{CC} = 6.0 V	21	10	-	ns
rec	recovery time	MR to CP, PL to CP; see Figure 10				
		V _{CC} = 2.0 V	50	14	-	ns
	V _{CC} = 4.5 V	10	5	-	ns	
		V _{CC} = 6.0 V	9	4	-	ns
su	set-up time	PE to CP; see Figure 11				
		V _{CC} = 2.0 V	75	22	-	ns
		V _{CC} = 4.5 V	15	8	-	ns
		V _{CC} = 6.0 V	13	6	-	ns
		TE to CP; see Figure 12				
		V _{CC} = 2.0 V	150	44	-	ns
		V _{CC} = 4.5 V	30	16	-	ns
		V _{CC} = 6.0 V	26	13	-	ns
		Pn to CP; see Figure 11				
		V _{CC} = 2.0 V	75	22	-	ns
		V _{CC} = 4.5 V	15	8	-	ns
		V _{CC} = 6.0 V	13	6	-	ns
h	hold time	PE to CP; see Figure 11				
		V _{CC} = 2.0 V	0	-14	-	ns
		V _{CC} = 4.5 V	0	-5	-	ns
		V _{CC} = 6.0 V	0	-4	-	ns
		TE to CP; see Figure 12				
		V _{CC} = 2.0 V	0	-30	-	ns
		$V_{CC} = 4.5 V$	0	-11	-	ns
		V _{CC} = 6.0 V	0	-9	-	ns
		Pn to CP; see Figure 11				
		V _{CC} = 2.0 V	0	-17	-	ns
		$V_{CC} = 4.5 V$	0	-6	-	ns
		$V_{\rm CC} = 6.0 \text{ V}$	0	-5	-	ns

Table 7. Dynamic characteristics ... continued GND = 0 V; $t_r = t_f = 6$ ns; $C_L = 50$ pF; see Figure 13.

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
f _{max}	maximum frequency	see Figure 7					
		V _{CC} = 2.0 V		3.0	10	-	MHz
		V _{CC} = 4.5 V		15	29	-	MHz
		V _{CC} = 6.0 V		18	35	-	MHz
		V _{CC} = 5.0 V; C _L = 15 pF		-	32	-	MHz
C _{PD}	power dissipation capacitance	$V_1 = GND$ to V_{CC}	<u>[3]</u>	-	24	-	pF
T _{amb} = -4	0 °C to +85 °C						
t _{pd}	propagation delay	CP to TC; see Figure 7	<u>[1]</u>				
		V _{CC} = 2.0 V		-	-	375	ns
		V _{CC} = 4.5 V		-	-	75	ns
		V _{CC} = 6.0 V		-	-	64	ns
		TE to TC; see Figure 8					
		V _{CC} = 2.0 V		-	-	220	ns
		$V_{CC} = 4.5 V$		-	-	44	ns
		V _{CC} = 6.0 V		-	-	37	ns
		PL to TC; see Figure 9					
		V _{CC} = 2.0 V		-	-	395	ns
		V _{CC} = 4.5 V		-	-	79	ns
		V _{CC} = 6.0 V		-	-	40	ns
t _{PHL}	HIGH to LOW	MR to TC; see Figure 9					
	propagation delay	V _{CC} = 2.0 V		-	-	345	ns
		V _{CC} = 4.5 V		-	-	69	ns
		V _{CC} = 6.0 V		-	-	59	ns
t _t	transition time	see Figure 8	[2]				
		V _{CC} = 2.0 V		-	-	95	ns
		V _{CC} = 4.5 V		-	-	19	ns
		V _{CC} = 6.0 V		-	-	16	ns
t _W	pulse width	CP HIGH or LOW; see Figure 7					
		V _{CC} = 2.0 V		205	-	-	ns
		V _{CC} = 4.5 V		41	-	-	ns
		V _{CC} = 6.0 V		35	-	-	ns
		MR LOW; see Figure 9					
		V _{CC} = 2.0 V		155	-	-	ns
		V _{CC} = 4.5 V		31	-	-	ns
		V _{CC} = 6.0 V		26	-	-	ns
		PL LOW; see Figure 9					
		V _{CC} = 2.0 V		155	-	-	ns
		V _{CC} = 4.5 V		31	-	-	ns
		$V_{CC} = 6.0 V$		26	-	-	ns

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Table 7. Dynamic characteristics ...continued

GND = 0 V	; $t_r = t_f = 6 \text{ ns}$; $C_L = 50 \text{ pF}$; see Figure 13	1
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rec}	recovery time	MR to CP, PL to CP; see Figure 10				
		V _{CC} = 2.0 V	65	-	-	ns
		V _{CC} = 4.5 V	13	-	-	ns
		V _{CC} = 6.0 V	11	-	-	ns
t _{su}	set-up time	PE to CP; see Figure 11				
		V _{CC} = 2.0 V	95	-	-	ns
		V _{CC} = 4.5 V	19	-	-	ns
		V _{CC} = 6.0 V	16	-	-	ns
		TE to CP; see Figure 12				
		V _{CC} = 2.0 V	190	-	-	ns
		V _{CC} = 4.5 V	38	-	-	ns
		V _{CC} = 6.0 V	33	-	-	ns
		Pn to CP; see Figure 11				
		V _{CC} = 2.0 V	95	-	-	ns
		V _{CC} = 4.5 V	19	-	-	ns
	V _{CC} = 6.0 V	16	-	-	ns	
t _h hold	hold time	PE to CP; see Figure 11				
		V _{CC} = 2.0 V	0	-	-	ns
		V _{CC} = 4.5 V	0	-	-	ns
		V _{CC} = 6.0 V	0	-	-	ns
		TE to CP; see Figure 12				
		V _{CC} = 2.0 V	0	-	-	ns
		V _{CC} = 4.5 V	0	-	-	ns
		V _{CC} = 6.0 V	0	-	-	ns
		Pn to CP; see Figure 11				
		V _{CC} = 2.0 V	0	-	-	ns
		V _{CC} = 4.5 V	0	-	-	ns
		V _{CC} = 6.0 V	0	-	-	ns
max	maximum frequency	see Figure 7				
		V _{CC} = 2.0 V	2.4	-	-	MHz
		V _{CC} = 4.5 V	12	-	-	MHz
		V _{CC} = 6.0 V	14	-	-	MHz

Table 7. Dynamic characteristics ...continued

GND = 0 V; $t_r = t_f = 6 ns$; $C_L = 50 pF$; see <u>Figure 13</u>.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
T _{amb} = -4	0 °C to +125 °C						
t _{pd}	propagation delay	CP to $\overline{\text{TC}}$; see Figure 7	<u>[1]</u>				
		V _{CC} = 2.0 V		-	-	450	ns
		V _{CC} = 4.5 V		-	-	90	ns
		V _{CC} = 6.0 V		-	-	77	ns
		TE to TC; see Figure 8					
		V _{CC} = 2.0 V		-	-	265	ns
		V _{CC} = 4.5 V		-	-	53	ns
		V _{CC} = 6.0 V		-	-	45	ns
		PL to TC; see Figure 9					
		V _{CC} = 2.0 V		-	-	475	ns
		V _{CC} = 4.5 V		-	-	95	ns
		V _{CC} = 6.0 V		-	-	81	ns
t _{PHL}	HIGH to LOW	MR to TC; see Figure 9					
	propagation delay	V _{CC} = 2.0 V		-	-	415	ns
		$V_{CC} = 4.5 V$		-	-	83	ns
		$V_{CC} = 6.0 V$		-	-	71	ns
t _t	transition time	see Figure 8	[2]				
		$V_{\rm CC} = 2.0$ V		-	-	110	ns
		V _{CC} = 4.5 V		-	-	22	ns
		V _{CC} = 6.0 V		-	-	19	ns
t _W	pulse width	CP HIGH or LOW; see Figure 7					
		V _{CC} = 2.0 V		250	-	-	ns
		V _{CC} = 4.5 V		50	-	-	ns
		V _{CC} = 6.0 V		43	-	-	ns
		MR LOW; see Figure 9					
		V _{CC} = 2.0 V		190	-	-	ns
		V _{CC} = 4.5 V		38	-	-	ns
		V _{CC} = 6.0 V		32	-	-	ns
		PL LOW; see Figure 9					
		V _{CC} = 2.0 V		190	-	-	ns
		$V_{CC} = 4.5 V$		38	-	-	ns
		$V_{\rm CC} = 6.0 \text{ V}$		32	-	-	ns
rec	recovery time	MR to CP, PL to CP; see Figure 10			<u> </u>		
	-	V _{CC} = 2.0 V		75	-	-	ns
		$V_{\rm CC} = 4.5 \text{ V}$		15	-	-	ns
		$V_{\rm CC} = 6.0 \text{ V}$		13	-	-	ns

Table 7.	Dynamic characteristics continued
$GND = 0$ \	/; $t_r = t_f = 6 \text{ ns}; C_L = 50 \text{ pF}; \text{ see } \frac{Figure 13}{2}$.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{su} s	set-up time	PE to CP; see Figure 11				
		V _{CC} = 2.0 V	110	-	-	ns
		V _{CC} = 4.5 V	22	-	-	ns
		V _{CC} = 6.0 V	19	-	-	ns
		TE to CP; see Figure 12				
		V _{CC} = 2.0 V	225	-	-	ns
		V _{CC} = 4.5 V	45	-	-	ns
		V _{CC} = 6.0 V	38	-	-	ns
		Pn to CP; see Figure 11				
		V _{CC} = 2.0 V	110	-	-	ns
		V _{CC} = 4.5 V	22	-	-	ns
		V _{CC} = 6.0 V		-	-	ns
t _h	hold time	PE to CP; see Figure 11				
		V _{CC} = 2.0 V	0	-	-	ns
		V _{CC} = 4.5 V	0	-	-	ns
		V _{CC} = 6.0 V	0	-	-	ns
		TE to CP; see Figure 12				
		V _{CC} = 2.0 V	0	-	-	ns
		V _{CC} = 4.5 V	0	-	-	ns
		V _{CC} = 6.0 V	0	-	-	ns
		Pn to CP; see Figure 11				
		V _{CC} = 2.0 V	0	-	-	ns
		V _{CC} = 4.5 V	0	-	-	ns
		V _{CC} = 6.0 V	0	-	-	ns
max	maximum frequency	see Figure 7				
		$V_{CC} = 2.0 V$	2.0	-	-	MHz
		$V_{CC} = 4.5 V$	10	-	-	MHz
		$V_{CC} = 6.0 V$	12	-	-	MHz

[1] t_{pd} is the same as t_{PHL} , t_{PLH} .

[2] t_t is the same as t_{THL} , t_{TLH} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \sum (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



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Test data is given in Table 8.

Definitions for test circuit:

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

 $\overset{}{\vdash}$

 \rightarrow

mna101

C_L = Load capacitance including jig and probe capacitance.

Fig 13. Test circuit for measuring switching times

Table 8. Test data

Supply	Input		Load
V _{CC}	VI	t _r , t _f	CL
2.0 V	V _{CC}	6 ns	50 pF
4.5 V	V _{CC}	6 ns	50 pF
6.0 V	V _{CC}	6 ns	50 pF
5.0 V	V _{CC}	6 ns	15 pF

13. Application information





14. Package outline



Fig 16. Package outline SOT109-1 (SO16)

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SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm SOT338-1 D Α X - [7] y = v 🕅 A HF Ζ 16 Q A₂ Ă (A₃) A_1 ¥ pin 1 index ŧ Lp 8 detail X 0 w (M . b_p е 2.5 5 mm 0 scale DIMENSIONS (mm are the original dimensions) Α E⁽¹⁾ Z⁽¹⁾ D⁽¹⁾ UNIT L Q θ A₁ A_2 A_3 bp с е Η_E Lp v w у max 7.9 0.38 0.20 1.03 8° 0.21 1.80 6.4 5.4 0.9 1.00 2 mm 0.25 0.65 1.25 0.2 0.13 0.1 0.05 1.65 0.25 0.09 6.0 5.2 7.6 0.63 0.7 0.55 0° Note 1. Plastic or metal protrusions of 0.25 mm maximum per side are not included. REFERENCES OUTLINE EUROPEAN ISSUE DATE VERSION PROJECTION JEDEC JEITA IEC 99-12-27 SOT338-1 MO-150 E ∃⊚ 03-02-19

Fig 17. Package outline SOT338-1 (SSOP16)

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Fig 18. Package outline SOT403-1 (TSSOP16)

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15. Abbreviations

Table 9. Abbreviations				
Acronym	Description			
CMOS	Complementary Metal Oxide Semiconductor			
DUT	Device Under Test			
ESD	ElectroStatic Discharge			
HBM	Human Body Model			
MM	Machine Model			

16. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC40103 v.4	20160127	Product data sheet	-	74HC40103 v.3
Modifications:	 Type numb 	er 74HC40103N (SOT38-4) re	moved.	
74HC40103 v.3	20041112	Product data sheet	-	74HC_HCT40103_CNV v.2
Modifications:	 The format of this data sheet has been redesigned to comply with the current presentation and information standard of Philips Semiconductors. 			
	 Removed t 	ype number 74HCT40103.		
	 Inserted fail 	mily specification.		
74HC_HCT40103_CNV v.2	19970918	Product specification	-	74HC_HCT40103 v.1
74HC_HCT40103 v.1	19901201	Product specification	-	-

17. Legal information

17.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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